

## **KSB601**

### **Low Frequency Power Amplifier**

- Medium Speed Switching Industrial Use
- Complement to KSD560

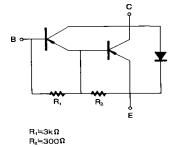


### 1.Base 2.Collector 3.Emitter

# **PNP Epitaxial Silicon Darlington Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	- 100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 100	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 7	V
I <sub>C</sub>	Collector Current (DC)	- 5	Α
I <sub>CP</sub>	*Collector Current (Pulse)	- 8	Α
I <sub>B</sub>	Base Current	- 0.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	1.5	W
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	30	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C



<sup>\*</sup> PW≤10ms, Duty Cycle≤50%

# Electrical Characteristics $\rm T_{C}{=}25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = - 3A, I <sub>B1</sub> = - 3mA, L = 1mH	100			V
V <sub>CEX</sub> (sus)1	Collector-Emitter Sustaining Voltage	$I_C = -3A$ , $I_{B1} = -I_{B2} = -3mA$ $V_{BE}(off) = 5V$ , $L = 180\mu H$ Clamped	- 100			V
V <sub>CEX</sub> (sus)2	Collector-Emitter Sustaining Voltage	$I_C = -6A$ , $I_{B1} = -12mA$ $I_{B2} = 3mA$ , $V_{BE}(off) = 5V$ L = 180uH, Clamped	- 100			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = - 100V, I <sub>E</sub> = 0			- 10	μΑ
I <sub>CER</sub>	Collector Cut-off Current	$V_{CE} = -100V, R_{BE} = 51\Omega$ $T_{C} = 125^{\circ}C$			- 1	mA
I <sub>CEX1</sub>	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$			- 10	μΑ
I <sub>CEX2</sub>	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$ $T_{C} = 125^{\circ}C$			- 1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = - 5V, I <sub>C</sub> = 0			- 3	mA
h <sub>FE1</sub> h <sub>FE2</sub>	*DC Current Gain	V <sub>CE</sub> = - 2V, I <sub>C</sub> = - 3A V <sub>CE</sub> = - 2V, I <sub>C</sub> = - 5A	2000 500		15000	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> = - 3A, I <sub>B</sub> = - 3mA			- 1.5	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	I <sub>C</sub> = - 3A, I <sub>B</sub> = - 3mA			- 2	V
t <sub>ON</sub>	Turn ON Time	V <sub>CC</sub> = - 50V , I <sub>C</sub> = - 3A		0.5		μs
t <sub>S</sub>	Storage	$I_{B1} = -I_{B2} = -3mA$		1		μs
t <sub>F</sub>	Fall time	$R_L = 17\Omega$		1		μs

<sup>\*</sup> Pulse Test: PW≤350μs, Duty Cycle≤2%

# $\mathbf{h}_{\text{FE}}$ Classification

Classification	R	0	Υ
h <sub>FE1</sub>	2000 ~ 5000	3000 ~ 7000	5000 ~ 15000

# **Typical Characteristics**

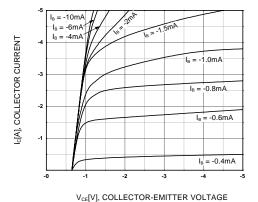


Figure 1. Static Characteristic

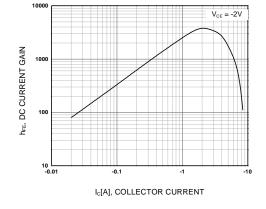


Figure 2. DC current Gain

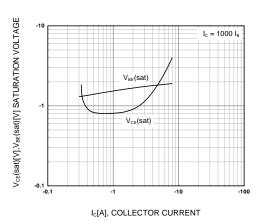


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

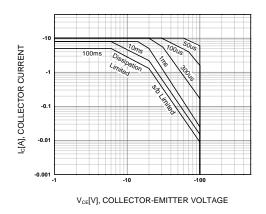


Figure 4. Safe Operating Area

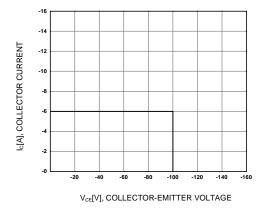


Figure 5. Reverse Bias Safe Operating Areas

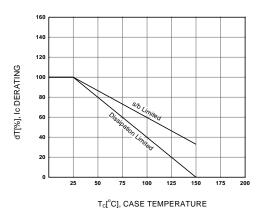


Figure 6. Derating Curve of Safe Operating Areas

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# Typical Characteristics (Continued)

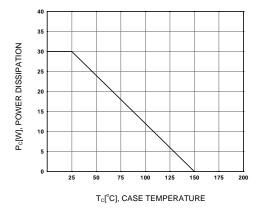
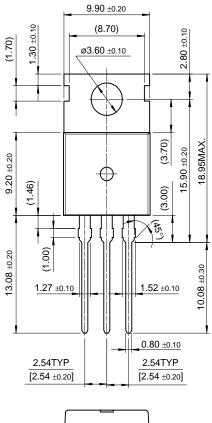


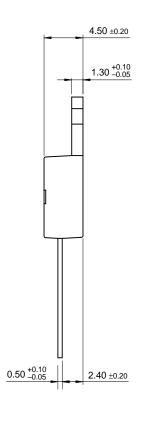
Figure 7. Power Derating

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# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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